

L Number	Hits	Search Text	DB	Time stamp
1	381	(hbt (heterostructure adj bipolar adj transistor)) and (sige (silicon near5 germanium))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 10:59
6	64	((hbt (heterostructure adj bipolar adj transistor)) and (sige (silicon near5 germanium))) and mesa	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 11:29
7	61	((hbt (heterostructure adj bipolar adj transistor)) and (sige (silicon near5 germanium))) and mesa) and dop\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 11:29
8	46	((hbt (heterostructure adj bipolar adj transistor)) and (sige (silicon near5 germanium))) and mesa) and dop\$3) and concentration	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 11:30
9	23	((hbt (heterostructure adj bipolar adj transistor)) and (sige (silicon near5 germanium))) and mesa) and dop\$3) and concentration) and depletion	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 12:02
10	7	((hbt (heterostructure adj bipolar adj transistor)) and (sige (silicon near5 germanium))) and mesa) and dop\$3) and concentration) and depletion) and strained	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 11:31
12	2	((hbt (heterostructure adj bipolar adj transistor)) and (sige (silicon near5 germanium))) and mesa) and dop\$3) and concentration) and (graded delta) near5 dop\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 11:33
11	2	((hbt (heterostructure adj bipolar adj transistor)) and (sige (silicon near5 germanium))) and mesa) and dop\$3) and concentration) and delta near5 dop\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 11:40
13	23	((hbt (heterostructure adj bipolar adj transistor)) and (sige (silicon near5 germanium))) and mesa) and dop\$3) and concentration) and depletion) and deplet\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 12:02

L Number	Hits	Search Text	DB	Time stamp
2	40	((hbt (heterostructure adj bipolar adj transistor)) and (sige (silicon near5 germanium))) and depletion near5 region	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 10:48
3	2	((hbt (heterostructure adj bipolar adj transistor)) and (sige (silicon near5 germanium))) and depletion near5 region) and strained near5 base	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 10:50
4	7	((hbt (heterostructure adj bipolar adj transistor)) and (sige (silicon near5 germanium))) and strained near5 base	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 10:51
1	381	(hbt (heterostructure adj bipolar adj transistor)) and (sige (silicon near5 germanium))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 10:59
6	64	((hbt (heterostructure adj bipolar adj transistor)) and (sige (silicon near5 germanium))) and mesa	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/30 11:00